

Jukka Viheriälä

List of Publications by Year in descending order

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Version: 2024-02-01

20
papers

216
citations

1163117

8
h-index

996975

15
g-index

20
all docs

20
docs citations

20
times ranked

173
citing authors

#	ARTICLE	IF	CITATIONS
1	Applications of UV-nanoimprint soft stamps in fabrication of single-frequency diode lasers. <i>Microelectronic Engineering</i> , 2009, 86, 321-324.	2.4	51
2	High power (60 mW) GaSb-based 1.9 μm superluminescent diode with cavity suppression element. <i>Applied Physics Letters</i> , 2016, 109, .	3.3	21
3	GaSb diode lasers tunable around 2.6 μm using silicon photonics resonators or external diffractive gratings. <i>Applied Physics Letters</i> , 2020, 116, .	3.3	21
4	High Spectral Purity High-Power GaSb-Based DFB Laser Fabricated by Nanoimprint Lithography. <i>IEEE Photonics Technology Letters</i> , 2016, 28, 1233-1236.	2.5	17
5	High-power temperature-stable GaInNAs distributed Bragg reflector laser emitting at 1180 nm. <i>Optics Letters</i> , 2016, 41, 657.	3.3	15
6	GaSb superluminescent diodes with broadband emission at 2.55 μm . <i>Applied Physics Letters</i> , 2018, 112, .	3.3	15
7	High Power 1.5 μm Pulsed Laser Diode With Asymmetric Waveguide and Active Layer Near p-cladding. <i>IEEE Photonics Technology Letters</i> , 2019, 31, 1635-1638.	2.5	14
8	Hybrid silicon photonics DBR laser based on flip-chip integration of GaSb amplifiers and μm -scale SOI waveguides. <i>Optics Express</i> , 2022, 30, 24995.	3.4	11
9	Low loss GaInNAs/GaAs gain waveguides with U-bend geometry for single-facet coupling in hybrid photonic integration. <i>Applied Physics Letters</i> , 2018, 113, 041104.	3.3	8
10	High-Power 1180-nm GaInNAs DBR Laser Diodes. <i>IEEE Photonics Technology Letters</i> , 2017, 29, 2023-2026.	2.5	7
11	High-power single mode GaSb-based 2 μm superluminescent diode with double-pass gain. <i>Applied Physics Letters</i> , 2019, 115, .	3.3	7
12	Multi-wavelength mid-IR light source for gas sensing. <i>Proceedings of SPIE</i> , 2017, , .	0.8	6
13	High-Power 1.5 μm Broad Area Laser Diodes Wavelength Stabilized by Surface Gratings. <i>IEEE Photonics Technology Letters</i> , 2018, 30, 1870-1873.	2.5	6
14	High-power 1550 nm tapered DBR laser diodes for LIDAR applications. , 2017, , .		5
15	High power GaInNAs superluminescent diodes emitting over 400 mW in the 1.2 μm wavelength range. <i>Applied Physics Letters</i> , 2019, 115, .	3.3	5
16	High-Power 1.5 μm Tapered Distributed Bragg Reflector Laser Diodes for Eye-Safe LIDAR. <i>IEEE Photonics Technology Letters</i> , 2020, 32, 1249-1252.	2.5	4
17	High-power 1.5 μm laser diodes for LIDAR applications. , 2019, , .		3
18	High Peak Power Laser Diodes for Eye Safe LIDAR with Integrated Wavelength Locking Element. , 2019, , .		0

#	ARTICLE	IF	CITATIONS
19	Design Strategies for Power Scaling of GaSb-Based Superluminescent Diodes for 2-3 μm Wavelength Range. , 2019, , .		0
20	GaSb-Based 2.55 μm External Cavity Diode Lasers Employing Ruled Diffraction Gratings and External Silicon Photonics Vernier Reflectors. , 2019, , .		0